

#### P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON) max</sub>	Package	I <sub>D</sub> T <sub>A</sub> = +25°C	
-20V	0.9Ω @ V <sub>GS</sub> = -4.5V	SOT23	-430mA	
-20V	2.0Ω @ V <sub>GS</sub> = -1.8V	30123	-150mA	

#### **Description**

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- DC-DC Converters
- · Power Management Functions

#### **Features**

- Low On-Resistance
- Very Low Gate Threshold Voltage V<sub>GS(TH)</sub> <1V</li>
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- ESD Protected Gate
- Qualified to AEC-Q101 standards for High Reliability

#### **Mechanical Data**

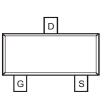
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding
- Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe.
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



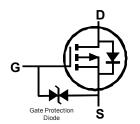


SOT23

Top View



Top View Internal Schematic



**Equivalent Circuit** 

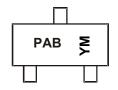
### Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP2004K-7	Standard	SOT23	3,000/Tape & Reel
DMP2004KQ-7	Automotive	SOT23	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



PAB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Year	2008		2009	2010		2011	2012	!	2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	I <sub>D</sub>	-600	mA
Pulsed Drain Current	I <sub>DM</sub>	-1.9	Α

# **Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	550	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	227	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

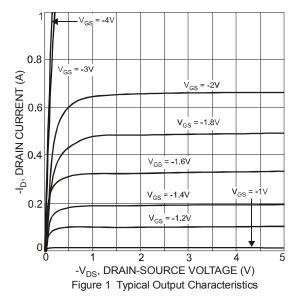
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 6)	•		•	•	•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±1.0	μA	$V_{GS} = \pm 4.5V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 6)	ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
		_	0.7	0.9		$V_{GS} = -4.5V$ , $I_{D} = -430$ mA		
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	1.1	1.4	Ω	$V_{GS} = -2.5V$ , $I_D = -300$ mA		
		_	1,7	2.0		$V_{GS} = -1.8V, I_D = -150mA$		
Forward Transfer Admittance	Y <sub>fs</sub>	200	_	_	mS	V <sub>DS</sub> = -10V, I <sub>D</sub> = -0.2A		
Diode Forward Voltage (Note 6)	$V_{SD}$	-0.5	_	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -115mA		
DYNAMIC CHARACTERISTICS (Note 7)								
Input Capacitance	C <sub>iss</sub>	_	_	175	pF			
Output Capacitance	Coss	_	_	30	pF	$V_{DS} = -16V, V_{GS} = 0V$ f = 1.0MHz		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	20	pF	-1 - 1.0WH 12		
Turn-On Delay Time	t <sub>D(on)</sub>	_	8.5	_	ns			
Turn-On Rise Time	t <sub>r</sub>	_	4.3	_	ns	$V_{DD} = -3V, V_{GS} = -2.5V,$		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	20.2	_	ns	$R_L = 300\Omega$ , $R_G = 25\Omega$ , $R_D = -100$ mA		
Turn-Off Fall Time	t <sub>f</sub>		19.2	_	ns	- I - I - I - I - I - I - I - I - I - I		

Notes:

- 5. Device mounted on FR-4 PCB.
- 6. Short duration pulse test used to minimize self-heating effect.
  7. Guaranteed by design. Not subject to product testing.





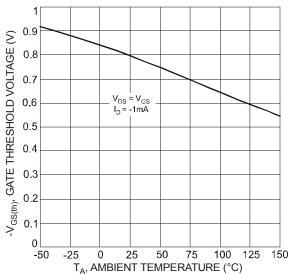




Figure 3 Gate Threshold Voltage vs. Ambient Temperature

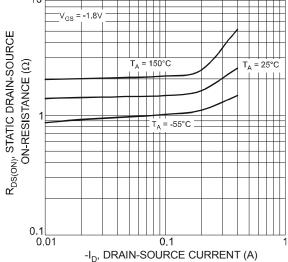
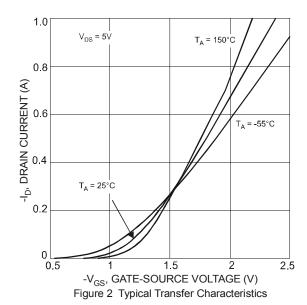
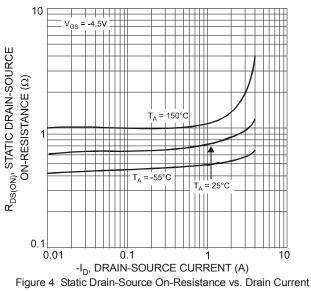


Figure 5 Static Drain-Source On-Resistance vs. Drain Current





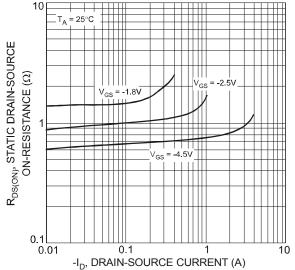


Figure 6 Static Drain-Source On-Resistance vs. **Drain-Source Current** 



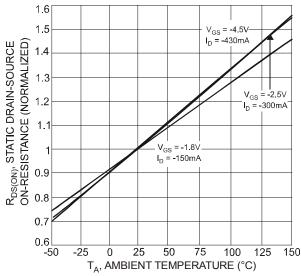


Figure 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

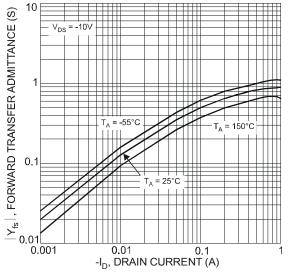


Figure 9 Forward Transfer Admittance vs. Drain Current

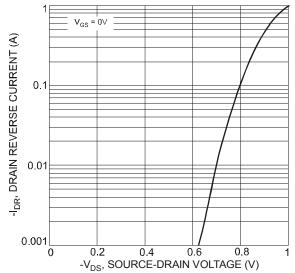
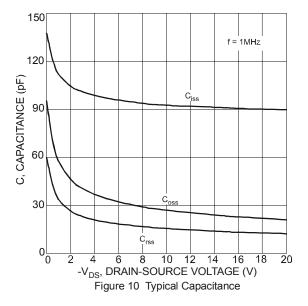


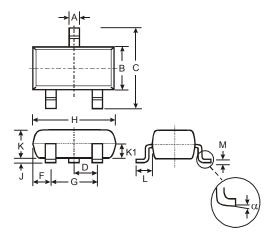
Figure 8 Reverse Drain Current vs. Source-Drain Voltage





# **Package Outline Dimensions**

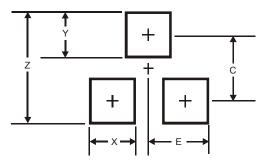
 $Please see AP02002 \ at \ http://www.diodes.com/datasheets/ap02002.pdf \ for \ the \ latest \ version.$ 



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	1	1	0.400					
L	0.45	0.61	0.55					
М	0.085	0.18	0.11					
α	0°	8°	-					
All Dimensions in mm								

# **Suggested Pad Layout**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	8.0
Y	0.9
C	2.0
F	1 35



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